

P-Channel 40-V (D-S), 175 °C MOSFET

PRODUCT SUMMARY

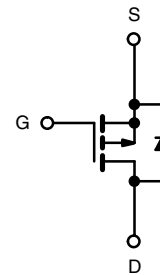
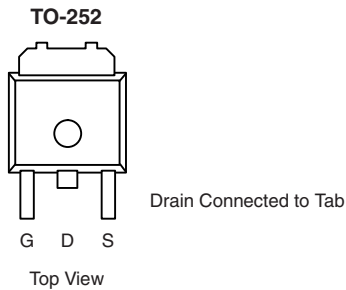
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
- 40	0.023 at $V_{GS} = 10$ V	- 20	20.6 nC
	0.030 at $V_{GS} = 4.5$ V	- 20	

FEATURES

- TrenchFET® Power MOSFET
- 100 % R_g Tested

APPLICATIONS

- LCD TV Inverter



Ordering Information: SUD50P04-23-E3 (Lead (Pb)-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 40	V
Gate-Source Voltage	V_{GS}	± 16	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	A
		$T_C = 100$ °C	
		$T_A = 25$ °C	
		$T_A = 100$ °C	
Pulsed Drain Current	I_{DM}	- 50	A
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C	
		$T_A = 25$ °C	
Single Pulse Avalanche Current	I_{AS}	- 20	
Avalanche Energy	E_{AS}	20	mJ
Maximum Power Dissipation	P_D	$T_C = 25$ °C	W
		$T_C = 100$ °C	
		$T_A = 25$ °C	
		$T_A = 100$ °C	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^b	R_{thJA}	40	48	°C/W
Maximum Junction-to-Case	R_{thJC}	2.75	3.3	

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

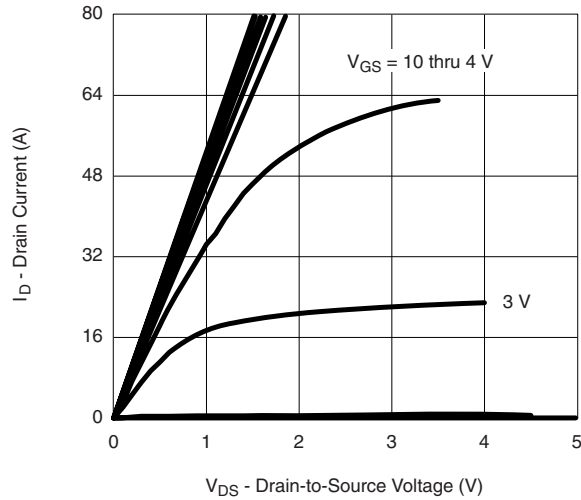
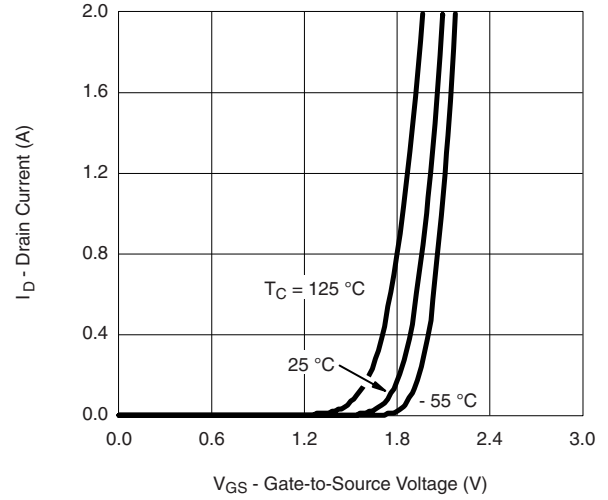
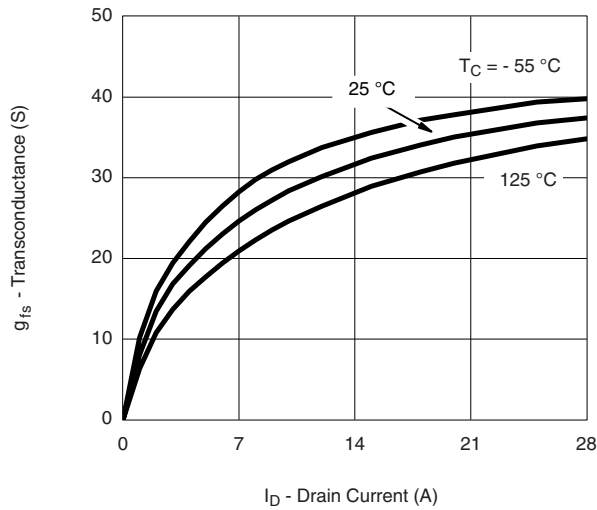
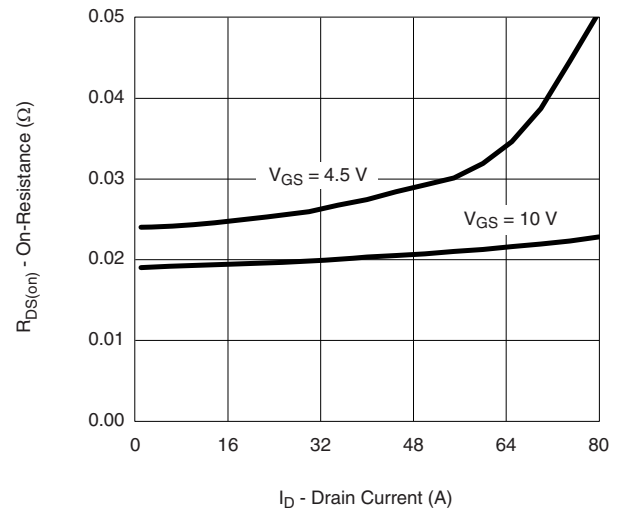
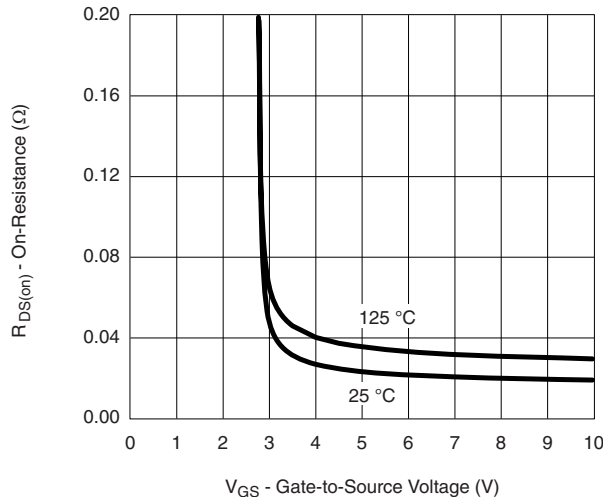
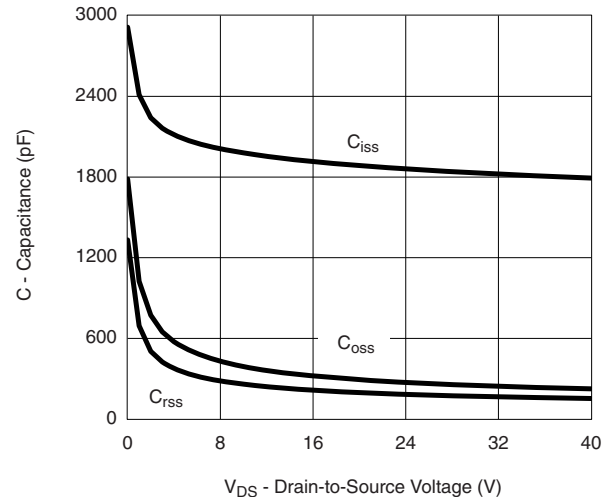
SPECIFICATIONS T _J = 25 °C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 40			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 40		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			3.7		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	-0.8		- 2	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 16 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 40 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 40 V, V _{GS} = 0 V, T _J = 100 °C			- 20	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ - 5 V, V _{GS} = - 10 V	- 30			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 15 A		0.019	0.023	Ω
		V _{GS} = - 4.5 V, I _D = - 10 A		0.024	0.030	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = - 15 A		30		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = - 20 V, V _{GS} = 0 V, f = 1 MHz		1880		pF
Output Capacitance	C _{oss}			286		
Reverse Transfer Capacitance	C _{rss}			192		
Total Gate Charge	Q _g	V _{DS} = - 20 V, V _{GS} = - 10 V, I _D = - 30 A		43.5	65	nC
		V _{DS} = - 20 V, V _{GS} = - 4.5 V, I _D = - 30 A		20.6	31	
Gate-Source Charge	Q _{gs}			4.6		
Gate-Drain Charge	Q _{gd}			7.6		
Gate Resistance	R _g	f = 1 MHz		3	5	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 20 V, R _L = 0.66 Ω I _D ≅ - 30 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		22	35	ns
Rise Time	t _r			217	325	
Turn-Off Delay Time	t _{d(off)}			42	65	
Fall Time	t _f			21	32	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 20 V, R _L = 0.66 Ω I _D ≅ - 30 A, V _{GEN} = - 10 V, R _g = 1 Ω		8	15	
Rise Time	t _r			12	20	
Turn-Off Delay Time	t _{d(off)}			36	55	
Fall Time	t _f			9	15	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 20	A
Pulse Diode Forward Current ^a	I _{SM}				- 50	
Body Diode Voltage	V _{SD}	I _S = - 10 A		- 0.85	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 20 A, dI/dt = 100 A/μs, T _J = 25 °C		44	66	ns
Body Diode Reverse Recovery Charge	Q _{rr}			53	80	nC
Reverse Recovery Fall Time	t _a			18		ns
Reverse Recovery Rise Time	t _b			26		

Notes:

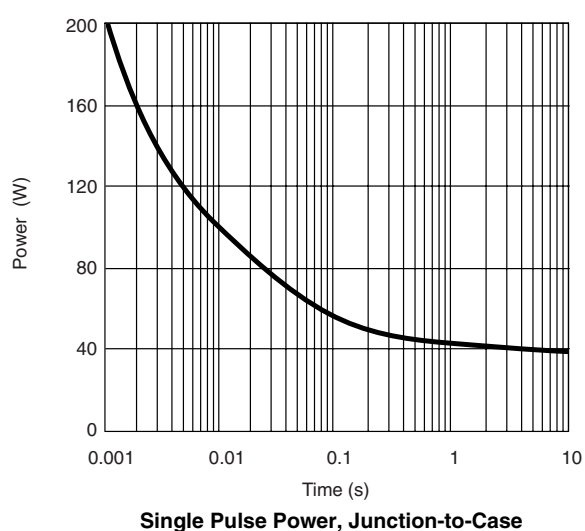
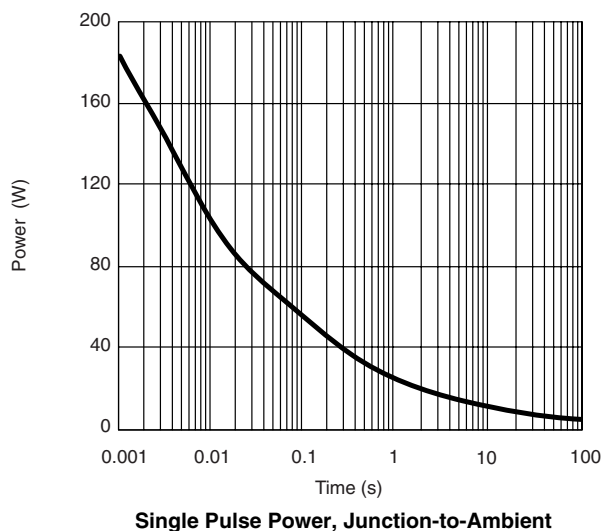
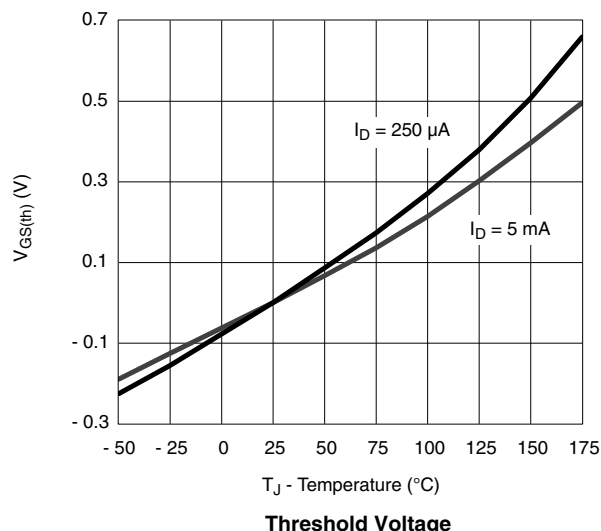
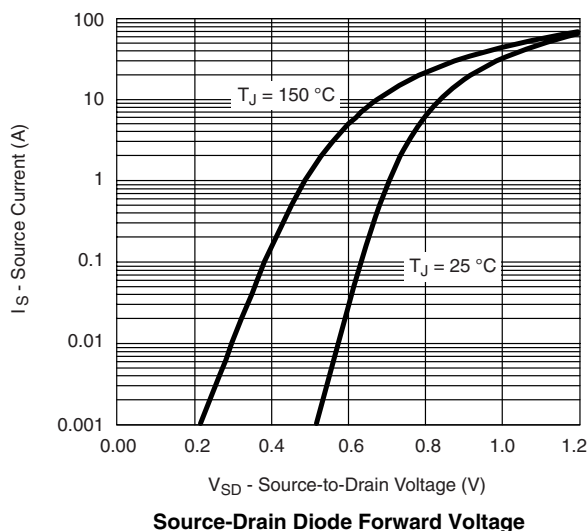
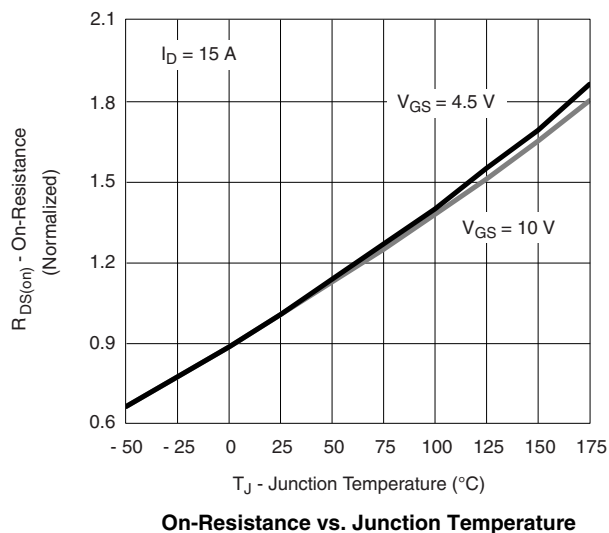
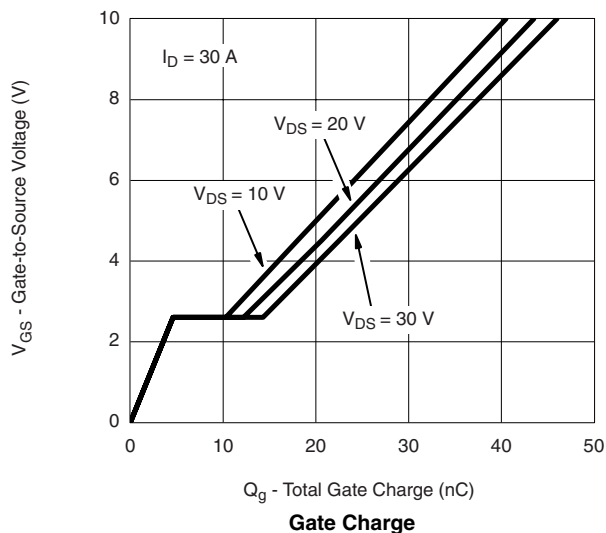
a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

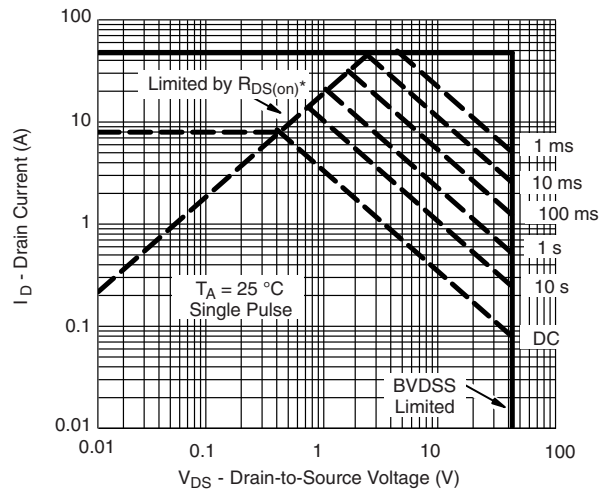
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

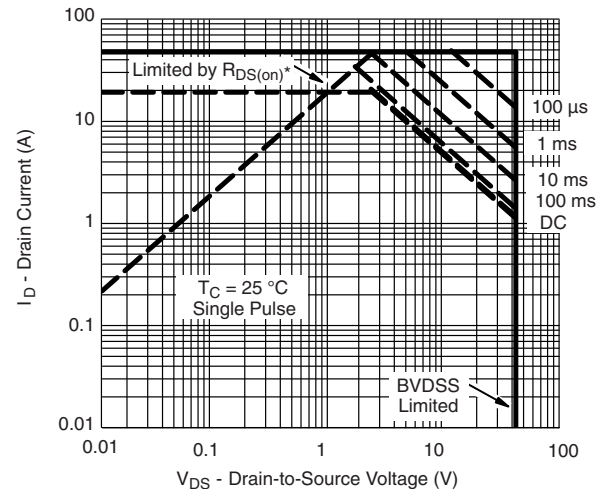
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

On-Resistance vs. Gate-to-Source Voltage

Capacitance

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

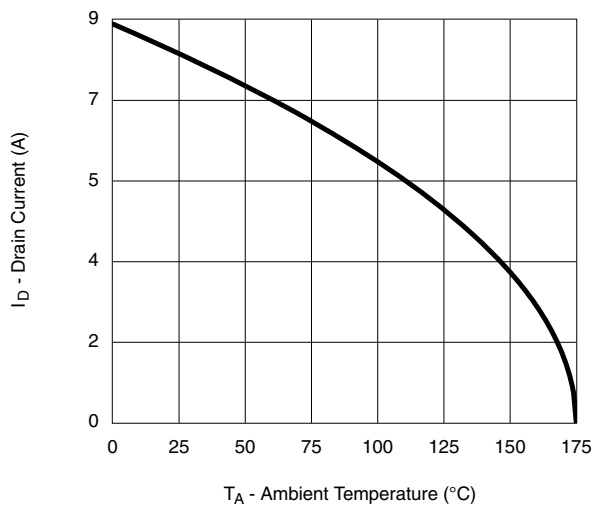


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted


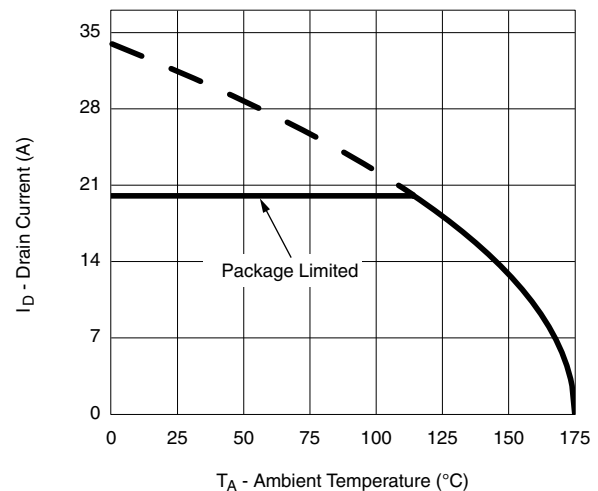
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Ambient



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified
Safe Operating Area, Junction-to-Case

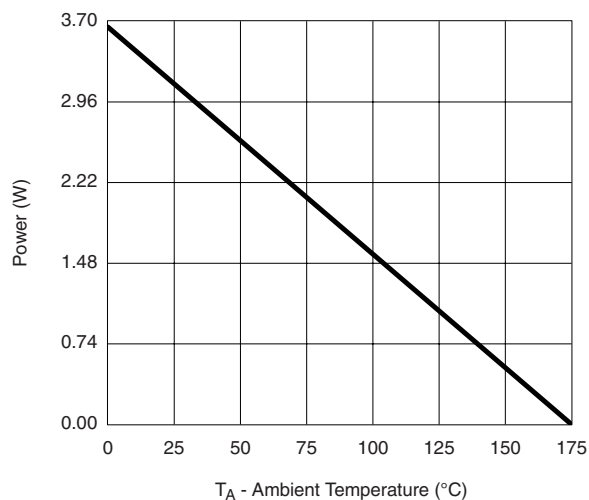
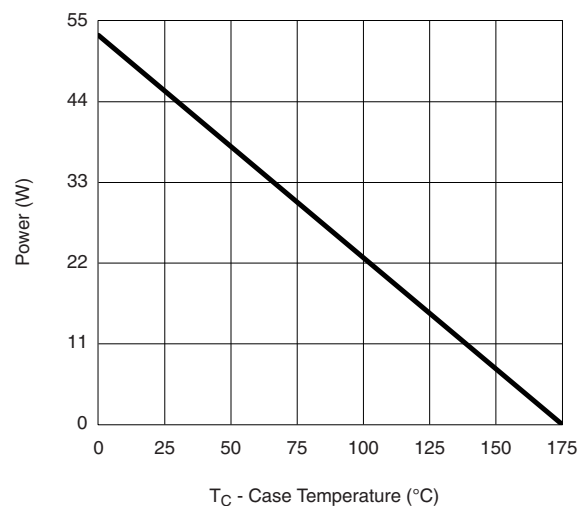


Current Derating, Junction-to-Ambient**

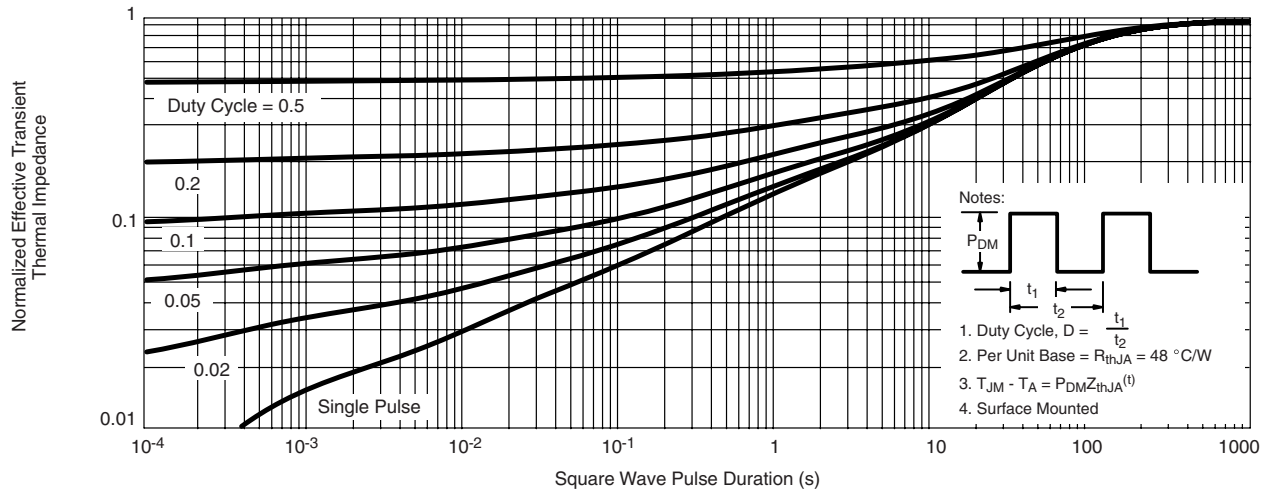
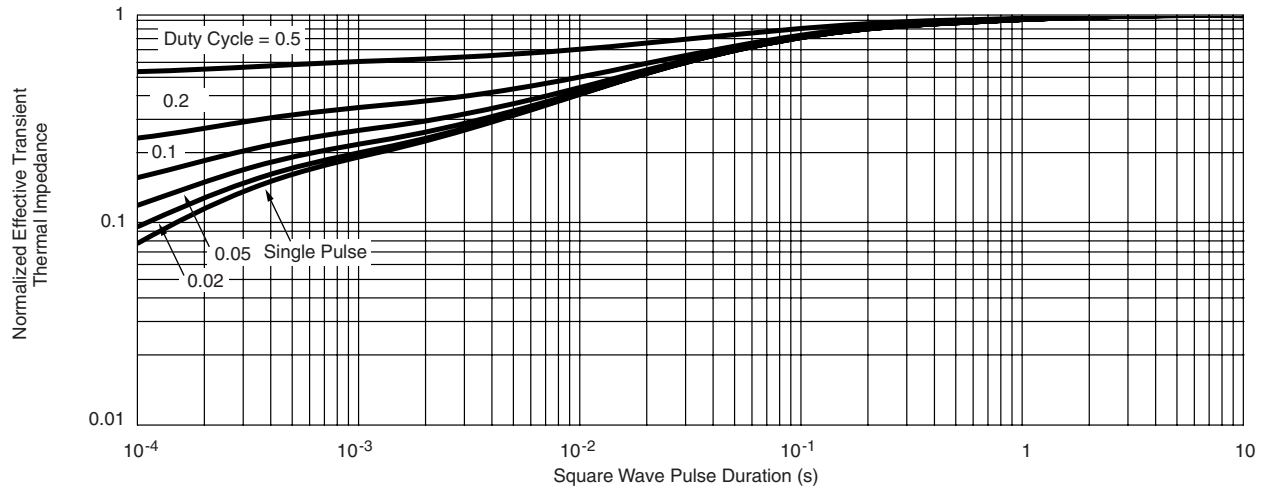


Current Derating, Junction-to-Case**

** The power dissipation P_D is based on $T_{J(max)} = 175^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Power Derating*, Junction-to-Ambient****Power Derating*, Junction-to-Case**

* The power dissipation P_D is based on $T_{J(max)} = 175$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Case

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